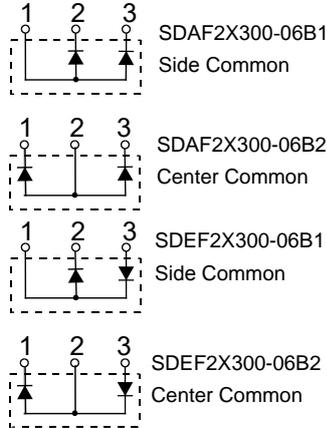
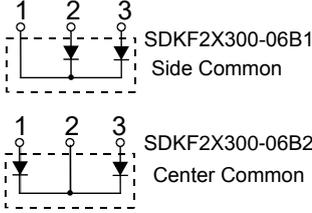
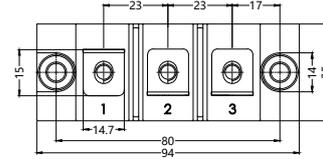
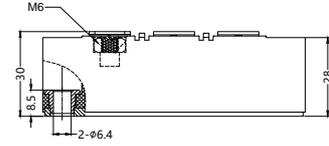


# SDKF/SDAF/SDEF2x300-06B1/B2

## Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules



Dimensions in mm (1mm=0.0394")



	VRSM V	VRRM V
SDKF2x300-06B1	600	600
SDKF2x300-06B2	600	600

	VRSM V	VRRM V
SDAF2x300-06B1	600	600
SDAF2x300-06B2	600	600

	VRSM V	VRRM V
SDEF2x300-06B1	600	600
SDEF2x300-06B2	600	600

Symbol	Test Conditions	Maximum Ratings	Unit
I <sub>FRMS</sub> I <sub>FAVM</sub> I <sub>FRM</sub>	T <sub>C</sub> =75°C T <sub>C</sub> =75°C; rectangular, d=0.5 t <sub>p</sub> <10us; rep. rating, pulse width limited by T <sub>VJM</sub>	430 2 x 300 1640	A
I <sub>FSM</sub>	T <sub>VJ</sub> =45°C t=10ms (50Hz), sine t=8.3ms (60Hz), sine	2400 2640	A
	T <sub>VJ</sub> =150°C t=10ms(50Hz), sine t=8.3ms(60Hz), sine	2160 2380	
I <sup>2</sup> t	T <sub>VJ</sub> =45°C t=10ms (50Hz), sine t=8.3ms (60Hz), sine	28800 29300	A <sup>2</sup> s
	T <sub>VJ</sub> =150°C t=10ms(50Hz), sine t=8.3ms(60Hz), sine	23300 23800	
T <sub>VJ</sub> T <sub>stg</sub> T <sub>Smax</sub>		-40...+150 -40...+125 110	°C
P <sub>tot</sub>	T <sub>C</sub> =25°C	875	W
V <sub>ISOL</sub>	50/60Hz, RMS t=1min I <sub>ISOL</sub> ≤1mA t=1s	3000 3600	V~
M <sub>d</sub>	Mounting torque (M6) Terminal connection torque (M6)	2.25-2.75/20-25 4.50-5.50/40-48	Nm/lb.in.
d <sub>s</sub> d <sub>A</sub> a	Creeping distance on surface Strike distance through air Maximum allowable acceleration	12.7 9.6 50	mm mm m/s <sup>2</sup>
Weight		170	g

**Sirectifier®**

# SDKF/SDAF/SDEF2x300-06B1/B2

## Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules

Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I <sub>R</sub>	T <sub>VJ</sub> =25°C; V <sub>R</sub> =V <sub>RRM</sub>		12	mA
	T <sub>VJ</sub> =25°C; V <sub>R</sub> =0.8·V <sub>RRM</sub>		3	
	T <sub>VJ</sub> =125°C; V <sub>R</sub> =0.8·V <sub>RRM</sub>		80	
V <sub>F</sub>	I <sub>F</sub> =150A; T <sub>VJ</sub> =125°C		1.05	V
	T <sub>VJ</sub> =25°C		1.27	
	I <sub>F</sub> =260A; T <sub>VJ</sub> =125°C		1.19	
	T <sub>VJ</sub> =25°C		1.36	
V <sub>TO</sub>	For power-loss calculations only		0.85	V
r <sub>T</sub>			1.34	mΩ
R <sub>thJH</sub> R <sub>thJC</sub>	DC current DC current		0.228 0.143	K/W
t <sub>rr</sub> I <sub>RM</sub>	I <sub>F</sub> =300A; T <sub>VJ</sub> =100°C V <sub>R</sub> =300V; T <sub>VJ</sub> =25°C -di/dt=400A/us; T <sub>VJ</sub> =100°C	250	300 44 66	ns A A

### FEATURES

- \* International standard package
- \* Copper base plate
- \* Planar passivated chips
- \* Short recovery time
- \* Low switching losses
- \* Soft recovery behaviour
- \* Isolation voltage 3600 V~
- \* RoHS compliant

### APPLICATIONS

- \* Antiparallel diode for high frequency switching devices
- \* Free wheeling diode in converters and motor control circuits
- \* Inductive heating and melting
- \* Uninterruptible power supplies (UPS)
- \* Ultrasonic cleaners and welders

### ADVANTAGES

- \* High reliability circuit operation
- \* Low voltage peaks for reduced protection circuits
- \* Low noise switching
- \* Low losses



# SDKF/SDAF/SDEF2x300-06B1/B2

## Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules

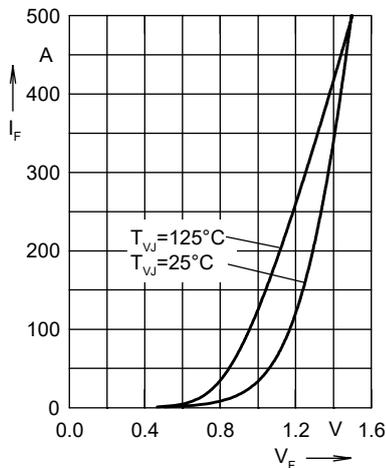


Fig. 1 Forward current  $I_F$  versus max. voltage drop  $V_F$  per leg

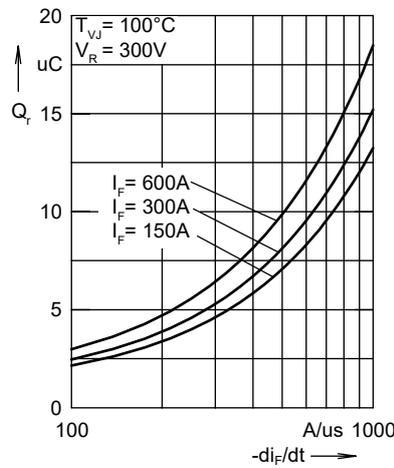


Fig. 2 Typ. reverse recovery charge  $Q_r$  versus  $-di_F/dt$

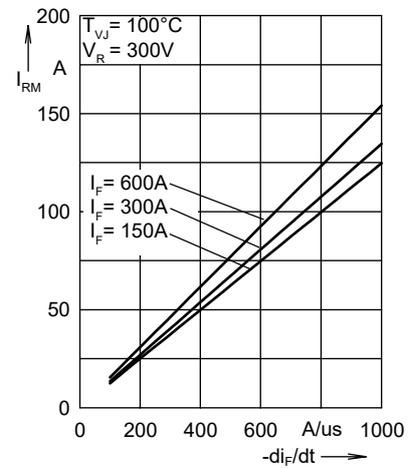


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$

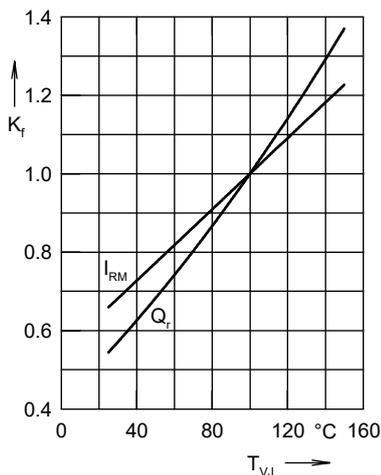


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus junction temperature  $T_{VJ}$

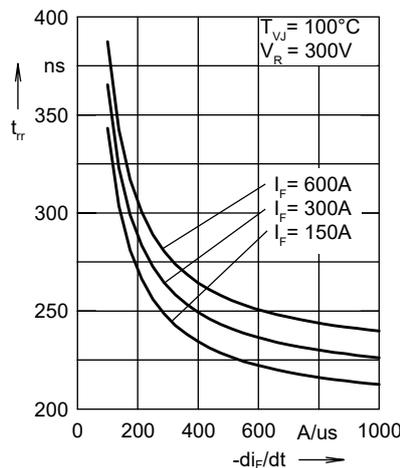


Fig. 5 Typ. recovery time  $t_{tr}$  versus  $-di_F/dt$

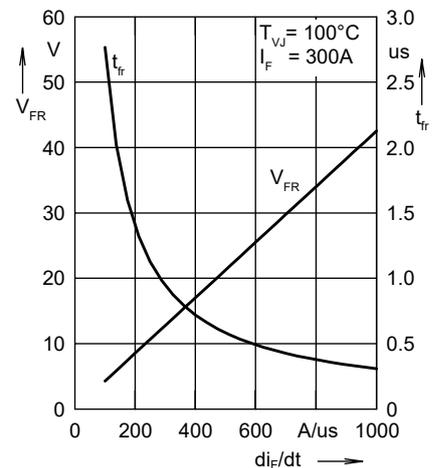


Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{tr}$  versus  $di_F/dt$

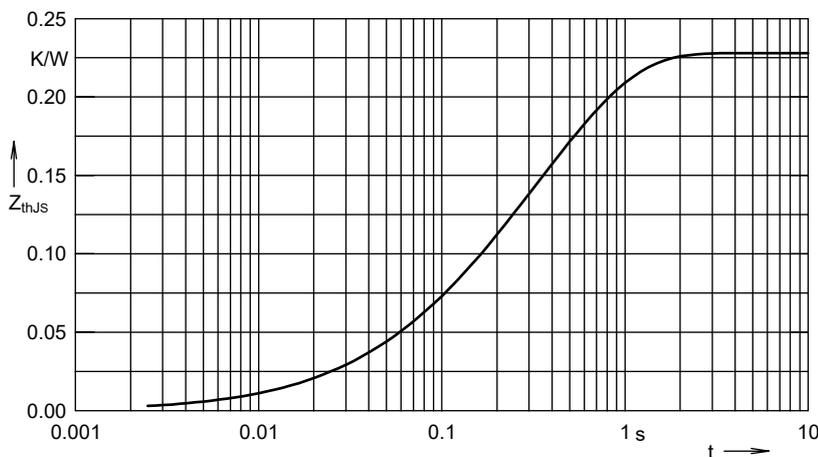


Fig. 7 Transient thermal impedance junction to heatsink

Constants for  $Z_{thJS}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.002	0.08
2	0.008	0.024
3	0.054	0.112
4	0.164	0.464